



Bipolar NPN Bare Die – BTN6019

Part Description

The BTN6019 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. PNP Complement is BTP6019.

Key Parameters:

- VCBO = 20V
- VCEO = 20V
- VEBO = 5V
- hFE = 500- @ VCE = 2V, IC = 0.1A
- VCE(Sat) = 0.45V @ IC = 3A, IB = 20mA
- fT = 150 MHz @ VCE = 5V, IE = 0A
- COBO = 22pF @ VCB = 10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to ZETEX / DIODES INC. FZT689

Die Size (Unawn)

1010 μ m X 1010 μ m, 40 Mils X 40 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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